

MM54HC182/MM74HC182 Look-Ahead Carry Generator

General Description

The MM54HC182/MM74HC182 is a high speed LOOK-AHEAD CARRY GENERATOR utilize advanced silicon-gate CMOS technology. It has the low power consumption and high noise immunity of standard CMOS integrated circuits, along with the ability to drive 10 LS-TTL loads.

These circuits are capable of anticipating a carry across four binary adders or groups of adders. They are cascadable to perform full look-ahead across n-bit adders. Carry, generate-carry, and propagate-carry functions are provided as shown in the pin designation table.

When used in conjunction with the HC181 arithmetic logic unit, these generators provide high-speed carry look-ahead capability for any word length. Each HC182 generates the look-ahead (anticipated carry) across a group of four ALU's and, in addition, other carry look-ahead circuits may be employed to anticipate carry across sections of four look-ahead packages up to n-bits. The method of cascading circuits to perform multi-level look-ahead is illustrated under typical application data.

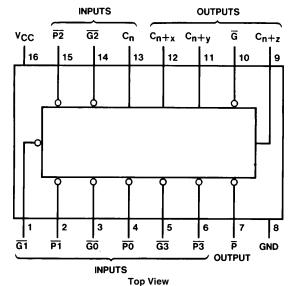
Carry input and output of the ALU's are in their true form, and the carry propagate (P) and carry generate (G) are in negated form; therefore, the carry functions (inputs, outputs, generate, and propagate) of the look-ahead generators are implemented in the compatible forms for direct connection to the ALU. Reinterpretations of carry functions as explained on the HC181 data sheet are also applicable to and compatible with the look-ahead generator.

Features

- TTL pinout compatible
- Typical propagation delay: 18 ns (clock to Q)
- Wide operating supply voltage range: 2-6V
- Low input current: 1 µA maximum
- Low quiescent supply current: 80 µA maximum (74HC Series)
- Fanout of 10 LS-TTL loads

Connection Diagram

Dual-In-Line Package



TL/F/5321-1

Order Number MM54HC182 or MM74HC182

Absolute Maximum Ratings (Notes 1 & 2) If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V _{CC})	-0.5 to $+7.0$ V
DC Input Voltage (V _{IN})	-1.5 to $V_{CC} + 1.5V$
DC Output Voltage (V _{OUT})	-0.5 to $V_{CC} + 0.5V$
Clamp Diode Current (I _{IK} , I _{OK})	\pm 20 mA
DC Output Current, per pin (IOUT)	\pm 25 mA
DC V _{CC} or GND Current, per pin (I _{CC})	\pm 50 mA
Storage Temperature Range (T _{STG})	-65°C to $+150$ °C
Power Dissipation (PD)	
(Note 3)	600 mW
S.O. Package only	500 mW

Operating Conditions								
	Min	Max	Units					
Supply Voltage (V _{CC})	2	6	V					
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V					
Operating Temp. Range (TA)								
MM74HC	-40	+85	°C					
MM54HC	-55	+125	°C					
Input Rise or Fall Times								
$(t_r, t_f) V_{CC} = 2.0V$		1000	ns					
$V_{CC} = 4.5V$		500	ns					
$V_{CC} = 6.0V$		400	ns					

DC Electrical Characteristics (Note 4)

Lead Temperature

(T_L) (Soldering 10 seconds)

Symbol	Parameter	Conditions	v _{cc}	T _A =25°C		74HC T _A = -40 to 85°C	54HC T _A = -55 to 125°C	Units
				Тур		Guaranteed		
V _{IH}	Minimum High Level Input Voltage		2.0V 4.5V 6.0V		1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V V V
V _{IL}	Maximum Low Level Input Voltage**		2.0V 4.5V 6.0V		0.5 1.35 1.8	0.5 1.35 1.8	0.5 1.35 1.8	V V V
V _{OH}	Minimum High Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 20 \mu A$	2.0V 4.5V 6.0V	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V V V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 4.0 \text{ mA}$ $ I_{OUT} \le 5.2 \text{ mA}$	4.5V 6.0V	4.2 5.7	3.98 5.48	3.84 5.34	3.7 5.2	V
V _{OL}	Maximum Low Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 20 \mu A$	2.0V 4.5V 6.0V	0 0 0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 4.0 \text{ mA}$ $ I_{OUT} \le 5.2 \text{ mA}$	4.5V 6.0V	0.2 0.2	0.26 0.26	0.33 0.33	0.4 0.4	V
I _{IN}	Maximum Input Current	V _{IN} =V _{CC} or GND	6.0V		±0.1	±1.0	±1.0	μΑ
Icc	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0V		8.0	80	160	μА

260°C

Note 4: For a power supply of 5V \pm 10% the worst case output voltages (V_{OH}, and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC}=5.5V and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

AC Electrical Characteristics $V_{CC} = 5V$, $T_A = 25$ °C, $C_L = 15$ pF, $t_f = t_f = 6$ ns

Symbol	Parameter	Conditions	Тур	Guaranteed Limit	Units
t _{PHL} , t _{PLH}	Maximum Propagation Delay - Pn to P		16	24	ns
t _{PHL} , t _{PLH}	Maximum Propagation Delay - Cn to any output		18	27	ns
t _{PHL} , t _{PLH}	Maximum Propagation Delay - Pn or Gn to any output		23	35	ns

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.

^{**} V_{IL} limits are currently tested at 20% of V_{CC}. The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics $V_{CC} = 2.0 V$ to 6.0 V, $C_L = 50$ pF, $t_f = t_f = 6$ ns (unless otherwise specified)

Symbol	Parameter	Conditions	v _{cc}	T _A =25°C		74HC T _A = -40 to 85°C	54HC T _A = -55 to 125°C	Units
				Тур		Guaranteed	Limits	
t _{PHL} , t _{PLH}	Maximum Propagation Delay Pn to P		2.0V 4.5V 6.0V	45 18 15	112 28 22	140 35 27	162 40 32	ns ns ns
t _{PHL} , t _{PLH}	Maximum Propagation Delay Cn to any output		2.0V 4.5V 6.0V	50 20 16	125 30 24	156 37 30	182 44 35	ns ns ns
t _{PHL} , t _{PLH}	Maximum Propagation Delay Pn or Gn to any output		2.0V 4.5V 6.0V	62 25 22	155 37 33	194 46 42	225 54 48	ns ns ns
t _{TLH} , t _{THL}	Maximum Output Rise and Fall Time		2.0V 4.5V 6.0V	25 7 6	75 15 13	95 19 16	110 22 19	ns ns ns
C _{PD}	Power Dissipation Capacitance			150				pF
C _{IN}	Maximum Input Capacitance			5	10	10	10	pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} \ V_{CC}^2 \ f + I_{CC} \ V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}$.

Logic Equations

 $C_{n+x} = G_0 + P_0 C_n$

 $C_{n+y} = G1 + P1 G0 + P1 P0 C_n$

 $C_{n+z} = G2 + P2 G1 + P2 P1 P0 C_n$

G=G3+P3 G2+P3 P2 G1+P3 P2 P1 G0

P=P3 P2 P1 P0

 $\overline{C}_{n+x} = \overline{Y0 (X0 + C_n)}$

 $\overline{C}_{n+y} = \overline{Y1 [X1 + Y0 (X0 + C_n)]}$

 $\overline{C}_{n+z} = \overline{Y2 \{X2+Y1 [X1+Y0 (X0+C_n)]\}}$

Y = Y3 (X3 + Y2) (X3 + X2 + Y1) (X3 + X2 + X1 + Y0)

X = X3 + X2 + X1 + X0

FUNCTION TABLE FOR $\overline{\mathbf{G}}$ OUTPUT

		OUTPUT						
G ₃	G2	G ₁	G ₀	P3	P2	P1	G	
L	Х	Х	Х	Х	Х	Х	L	
Х	L	Χ	Χ	L	Χ	Χ	L	
Х	Χ	L	Χ	L	L	Χ	L	
Х	Χ	Χ	L	L	L	L	L	
	All other combinations							

FUNCTION TABLE FOR \overline{P} OUTPUT

	INP	OUTPUT		
P3	P2	P1	P0	P
L	L	L	L	L
	All c mbir	н		

FUNCTION TABLE FOR C_{n+x} OUTPUT

II	NPUT	OUTPUT	
G ₀	P0	C _{n+x}	
L	Х	Х	Н
Х	L	Н	Н
Α	ll oth	1	
com	nbina	_	

FUNCTION TABLE FOR \boldsymbol{C}_{n+z} OUTPUT

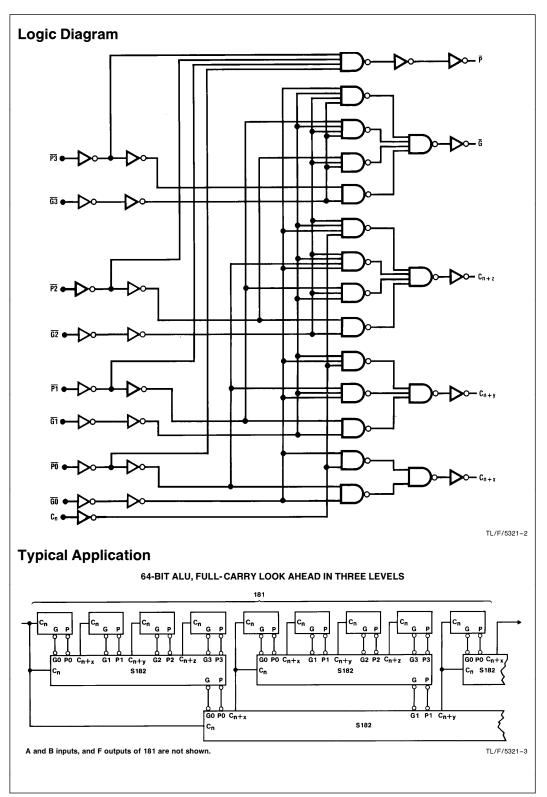
	INPUTS									
G ₂	G ₁	G ₀	P2	₽1	P0	Cn	C _{n+z}			
L	Х	Χ	Х	Х	Х	Х	Н			
Х	L	Χ	L	Χ	Χ	Χ	Н			
Х	Χ	L	L	L	Χ	Χ	Н			
Х	Χ	Χ	L	L	L	Н	Н			
	All other combinations									

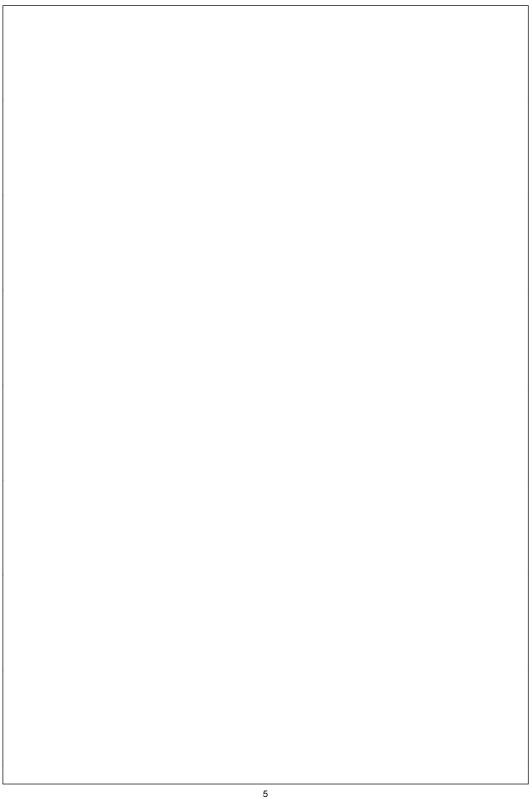
H=high level L=low level X=irrelevant

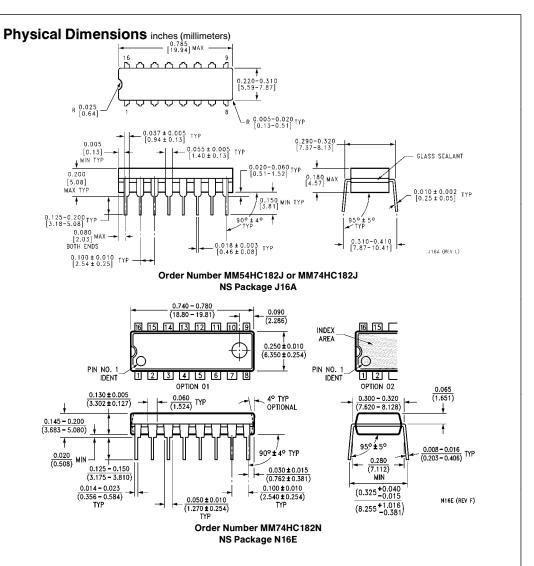
Any inputs not shown in a given table are irrelevant with respect to that output.

FUNCTION TABLE FOR $C_{n+\nu}$ OUTPUT

,								
	IN	OUTPUT						
G ₁	G ₀	₽1	P0	C_{n}	C _{n+y}			
L	Χ	Χ	Χ	Χ	Н			
Х	L	L	Χ	Χ	Н			
Χ	Χ	L	L	Н	Н			
	Al com	L						







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